# TriQuint ( semiconductor

#### **Applications**

- Point-to-Point Radio
- X-Band Communications



QFN 5x5mm 24L

#### **Product Features**

• Frequency Range: 10 – 12 GHz

• TOI: 43 dBm

• Power: 34.5 dBm Psat, 33 dBm P1dB

• Gain: 24 dB

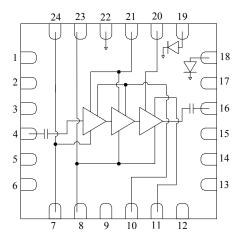
• Return Loss: 15 dB

Integrated Power Detector

• Bias: Vd = 6 V, Id = 1.3 A, Vg = -0.55 V Typical

• Package Dimensions: 5.0 x 5.0 x 0.85 mm

#### **Functional Block Diagram**



#### **General Description**

The TriQuint TGA2535-SM is a X-Band Packaged Power Amplifier. The TGA2535-SM operates from 10 to 12 GHz and is designed using TriQuint's power pHEMT production process.

The TGA2535-SM typically provides 43dBm of TOI at 20dBm Pout/Tone, 33 dBm of output power at 1dB gain compression, and the small signal gain is 24 dB.

The TGA2535-SM is available in a low-cost, surface mount 24 lead 5x5 QFN package and is ideally suited for Point-to-Point Radio, and X-Band Communications.

Lead-free and RoHS compliant

Evaluation Boards are available upon request.

# **Pin Configuration**

Pin #	Symbol
1, 2, 3, 5, 6, 9, 12, 13, 14, 15, 17	N/C
4	RF IN
7, 8, 23, 24	Vg
16	RF OUT
10, 11, 20, 21	Vd
18	Vref
19	Vdet
22	GND

#### **Ordering Information**

Part No.	<b>ECCN</b>	Description		
TGA2535-SM	3A001.b.2.b	X-band Power Amplifier		
Standard T/R size = 500 pieces on a 7" reel.				

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#### **Specifications**

#### **Absolute Maximum Ratings**

Parameter	Rating
Drain Voltage,Vd	+8 V
Gate Voltage,Vg	-3 to 0 V
Drain Current, Id	2.24 A
Gate Current, Ig	-11 to 90 mA
Power Dissipation, Pdiss	17.9 W
RF Input Power, CW, $50\Omega$ , T = $25^{\circ}$ C	27 dBm
Channel Temperature, Tch	200 °C
Mounting Temperature (30 Seconds)	260 °C
Storage Temperature	-40 to 150 °C

Operation of this device outside the parameter ranges given above may cause permanent damage. These are stress ratings only, and functional operation of the device at these conditions is not implied.

#### **Recommended Operating Conditions**

Parameter	Min	Typical	Max	Units
Vd		6		V
Id		1.3		A
Id_drive (Under RF Drive)		1.6		A
Vg		-0.55		V

Electrical specifications are measured at specified test conditions. Specifications are not guaranteed over all recommended operating conditions.

#### **Electrical Specifications**

Test conditions unless otherwise noted: 25°C, Vd = 6 V, Id = 1.3 A, Vg = -0.55 V Typical.

Test conditions diffess otherwise noted. 25 c, va o	,,14 1.511, , 5	o.ss v ryprour.		
Parameter	Min	Typical	Max	Units
Operational Frequency Range	10.0		12.0	GHz
Gain	20.5	24		dB
Input Return Loss	was translated at	-15	-10	dB
Output Return Loss		-15	-12	dB
Output Power @ Saturation	33	34.5		dBm
Output Power @ 1 dB Gain Compression	31.5	33		dBm
Output TOI @ Pout/Tone = 20 dBm	41	43		dBm
Noise Figure		10		dB
Gain Temperature Coefficient		-0.031		dB/°C
Power Temperature Coefficient		-0.004		dBm/°C

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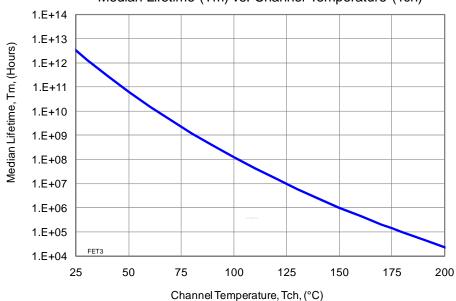


# **Specifications (cont.)**

# Thermal and Reliability Information

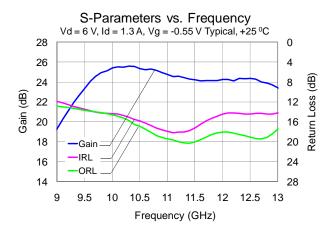
Parameter	Condition	Rating
Thermal Resistance, $\theta_{JC}$ , measured to back of package	Tbase = 85 °C	$\theta_{\rm JC} = 5.77  ^{\circ}{\rm C/W}$
Channel Temperature (Tch), and Median Lifetime (Tm)	Tbase = $85  ^{\circ}$ C, Vd = $6  \text{V}$ , Id = $1.3  \text{A}$ ,	Tch = 130 °C
Channel Temperature (TCII), and Median Enermie (TIII)	Pdiss = 7.8 W	Tm = 5.9 E+6 Hours
Channel Temperature (Tch), and Median Lifetime (Tm)	Tbase = 85 °C, Vd = 6 V, Id = 1.6 A,	Tch = 124 °C
Under RF Drive	Pout = $34.5 \text{ dBm}$ , Pdiss = $6.78 \text{ W}$	Tm = 1.0 E+7 Hours

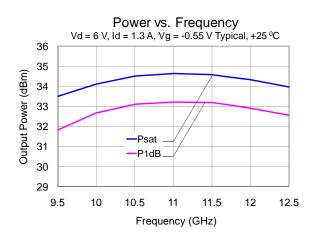
#### Median Lifetime (Tm) vs. Channel Temperature (Tch)

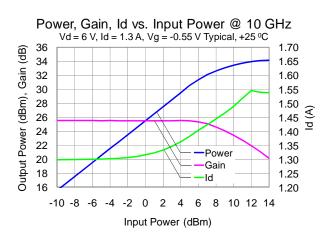


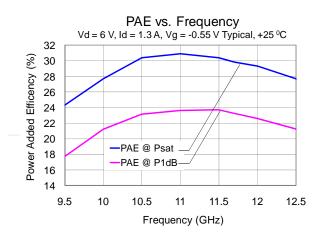


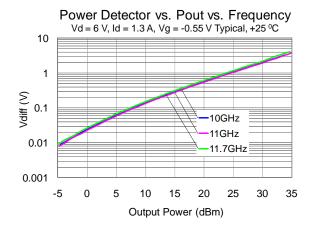
#### **Typical Performance**

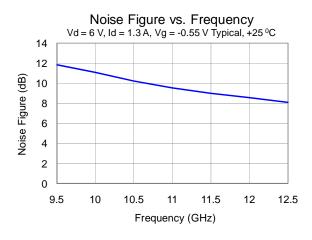






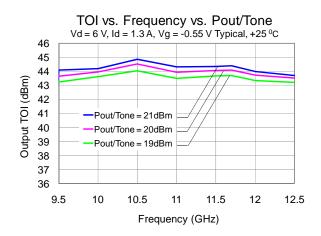


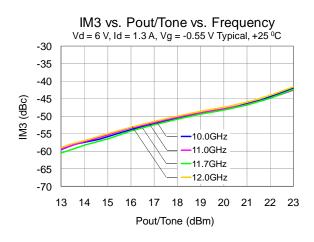


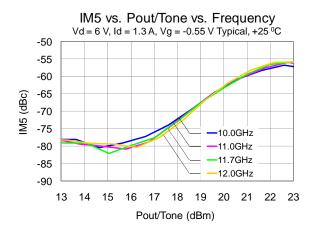


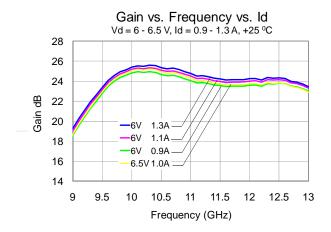


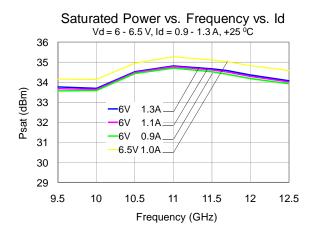
# **Typical Performance (cont.)**

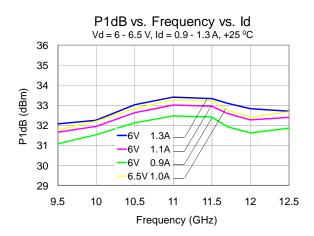












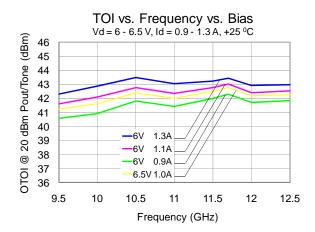
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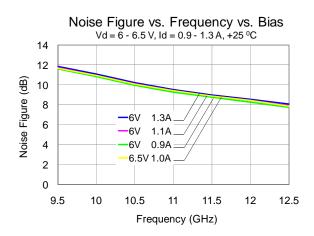
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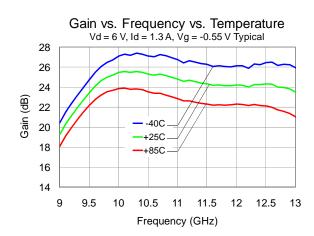
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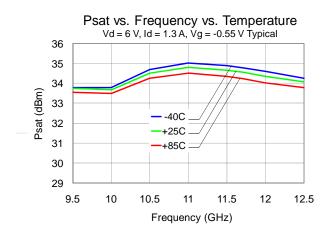


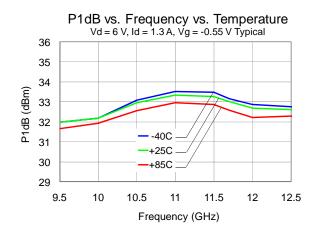
### **Typical Performance (cont.)**

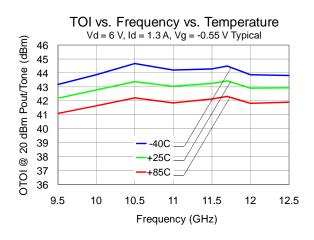












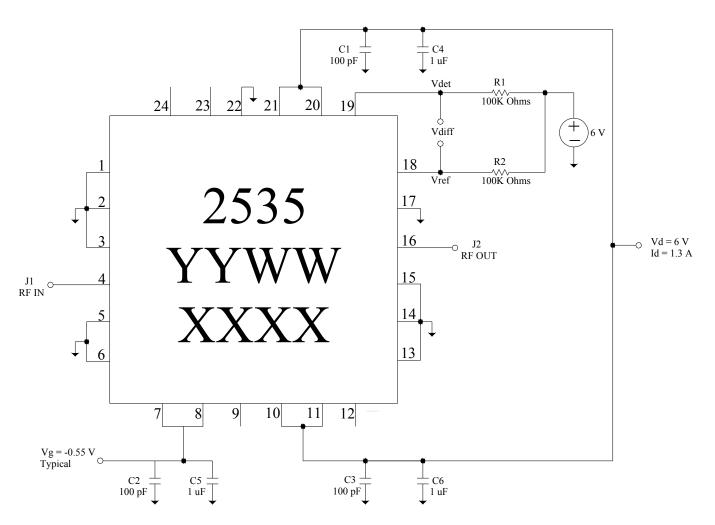
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# **Application Circuit**



Vg can be biased from either side (pins 7 and 8 or pins 23 and 24), and the non-biased side can be left open. Vd must be biased from both sides (pins 10, 11, 20, and 21).

Bias-up Procedure	Bias-down Procedure
Vg set to -1.5 V	Turn off RF supply
Vd set to +6 V	Reduce Vg to -1.5V. Ensure Id ~ 0 mA
Adjust Vg more positive until quiescent Id is 1.3A. This will be $\sim$ Vg = -0.55 V	Turn Vd to 0 V
Apply RF signal to RF Input	Turn Vg to 0 V

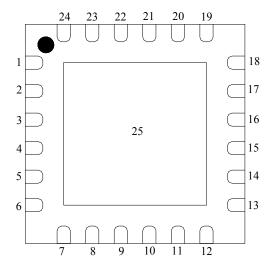
The TGA2535-SM will be marked with the "2535" designator and a lot code marked below the part designator. The "YY" represents the last two digits of the year the part was manufactured, the "WW" is the work week, and the "XXXX" is an autogenerated number.

# **TGA2535-SM**

X-Band Power Amplifier



# **Pin Description**



Pin	Symbol	Description	
1, 2, 3, 5, 6, 13, 14, 15, 17	N/C	No internal connection; must be grounded on PCB	
4	RF IN	Input, matched to 50 ohms	
7, 8, 23, 24	Vg	Gate voltage. ESD protection included; Bias network is required; can be biased from either side (pins 7 and 8 or pins 23 and 24), and non-biased side can be left opened; see Application Circuit on page 7 as an example.	
9, 12	N/C	No internal connection; can be grounded on PCB or left open	
10, 11, 20, 21	Vd	Drain voltage. Bias network is required; must be biased from both sides; see Application Circuit on page 7 as an example.	
16	RF OUT	Output, matched to 50 ohms	
18	Vref	Reference diode output voltage	
19	Vdet	Detector diode output voltage; varies with RF output power	
22	GND	Internal grounding; can be grounded on PCB or left open	
25	GND	Backside Paddle. Multiple vias should be employed to minimize inductance and thermal resistance; see Mounting Configuration on page 11 for suggested footprint.	

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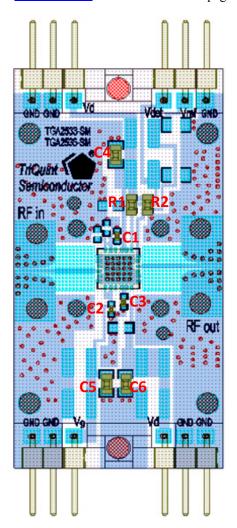
#### **Applications Information**

#### **PC Board Layout**

Top RF layer is 0.008" thick Rogers RO4003,  $\epsilon_r$  = 3.38. Metal layers are 1-oz copper. Microstrip 50  $\Omega$  line detail: width = 0.0175".

The pad pattern shown has been developed and tested for optimized assembly at TriQuint Semiconductor. The PCB land pattern has been developed to accommodate lead and package tolerances. Since surface mount processes vary from company to company, careful process development is recommended.

For further technical information, refer to the <u>TGA2533-SM</u> Product Information page.



#### **Bill of Material**

Ref Des	Value	Description	Manufacturer	Part Number
C1, C2, C3	100 pF	Cap, 0402, 50 V, 5%, COG	various	
C4, C5, C6	1 uF	Cap, 0603, 25 V, 10%, X5R	various	
R1, R2	100K Ohms	Res, 0603, 0.1 W, 5%, SMD	various	

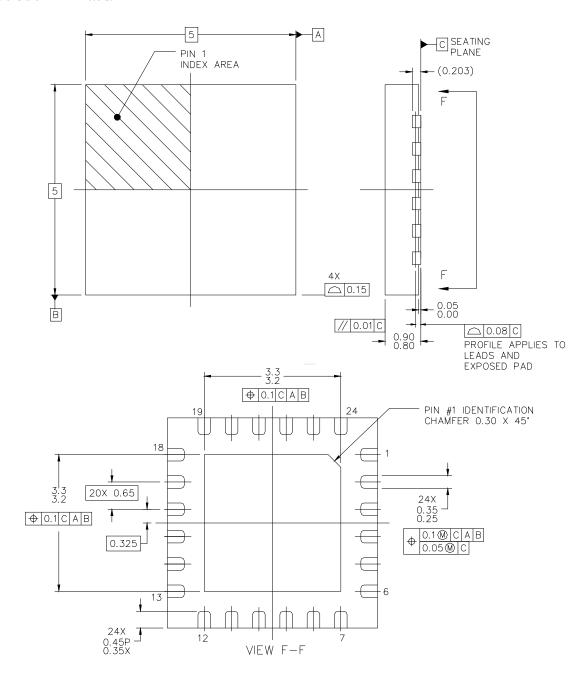
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#### **Mechanical Information**

#### **Package Information and Dimensions**

All dimensions are in millimeters.



This package is lead-free/RoHS-compliant with a copper alloy base (CDA194), and the plating material on the leads is 100% matte Sn. It is compatible with both lead-free (maximum 260 °C reflow temperature) and tin-lead (maximum 245 °C reflow temperature) soldering processes.



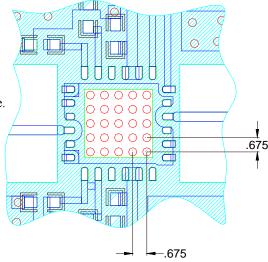
#### **Mechanical Information (cont.)**

#### **Mounting Configuration**

All dimensions are in millimeters (inches).

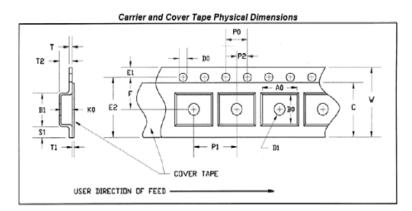
#### Notes:

- 1. A heatsink underneath the area of the PCB for the mounted device is recommended for proper thermal operation.
- 2. Ground / thermal vias are critical for the proper performance of this device. Vias have a final plated thru diameter of .40 mm (.016").



#### **Tape and Reel Information**

Tape and reel specifications for this part are also available on the TriQuint website in the "Application Notes" section. Standard T/R size = 500 pieces on a 7" x 0.5" reel.



#### **CARRIER AND COVER TAPE DIMENSIONS**

Part	Feature	Symbol	Size (in)	Size (mm)
Cavity	Length	A0	0.207	5.25
	Width	B0	0.207	5.25
	Depth	K0	0.043	1.10
	Pitch	P1	0.315	8.00
Distance Between Centerline	Cavity to Perforation Length Direction	P2	0.079	2.00
	Cavity to Perforation Width Direction	F	0.217	5.50
Cover Tape	Width	С	0.374	9.5
Carrier Tape	Width	W	0.472	12.0

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#### **Product Compliance Information**

#### **ESD Information**



#### **Caution! ESD-Sensitive Device**

ESD Rating: Class 0

Value: ≥ 200 V and < 250 V
Test: Human Body Model (HBM)
Standard: JEDEC Standard JESD22-A114

#### **MSL Rating**

Level 1 at +260 °C convection reflow The part is rated Moisture Sensitivity Level 1 at 260°C per JEDEC standard IPC/JEDEC J-STD-020.

#### **Solderability**

Compatible with the latest version of J-STD-020, Lead free solder, 260°C

This part is compliant with EU 2002/95/EC RoHS directive (Restrictions on the Use of Certain Hazardous Substances in Electrical and Electronic Equipment).

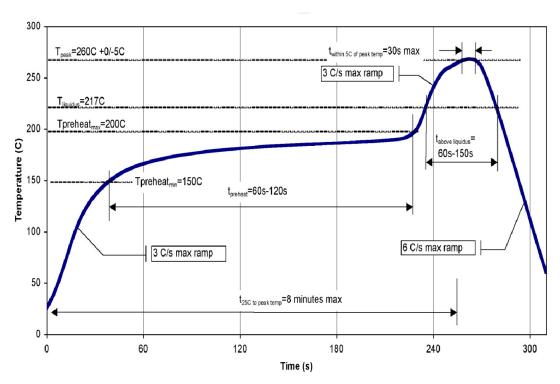
This product also has the following attributes:

- Lead Free
- Halogen Free (Chlorine, Bromine)
- Antimony Free
- TBBP-A  $(C_{15}H_{12}Br_4O_2)$  Free
- PFOS Free
- SVHC Free

#### **ECCN**

US Department of Commerce 3A001.b.2.b

#### **Recommended Soldering Temperature Profile**



# **TGA2535-SM**

X-Band Power Amplifier



#### **Contact Information**

For the latest specifications, additional product information, worldwide sales and distribution locations, and information about TriQuint:

Web: <u>www.triquint.com</u> Tel: +1.972.994.8465 Email: <u>info-sales@tqs.com</u> Fax: +1.972.994.8504

For technical questions and application information:

Email: info-networks@tqs.com

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